

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-9. (Canceled)

10. (Currently Amended) A method for producing a single crystal by Czochralski method by pulling a seed crystal from a raw material melt, comprising:

immersing the seed crystal into the raw material melt; and

growing the single crystal by rotating and pulling the seed crystal,

wherein:

the single crystal is pulled while controlling a value of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$)

within a range of values of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$); and

the range of values of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$), including a defect region and/or a defect-free region, is controlled according to T_{max} ($^{\circ}\text{C}$);

wherein:

$V(\text{mm}/\text{min})$ is a single crystal pulling rate of pulling the single crystal;

$G (\text{K}/\text{mm})$ is a temperature gradient at a solid-liquid interface, in a range of a melting point of the raw material and 1400°C ;

$T_{\text{max}} (^{\circ}\text{C})$ is a highest temperature of the raw material melt at an interface between a quartz crucible inner wall and the raw material melt; and

the range of values of V/G ($\text{mm}^2/\text{K} \cdot \text{min}$) is ~~selected from the group~~ consisting of:

(A) from $-0.000724 [\text{mm}^2/(^{\circ}\text{C} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (^{\circ}\text{C}) + 1.31$ ($\text{mm}^2/\text{K} \cdot \text{min}$) to less than $-0.000724 [\text{mm}^2/(^{\circ}\text{C} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (^{\circ}\text{C}) + 1.38$ ($\text{mm}^2/\text{K} \cdot \text{min}$); or

$$(B) -0.000724 [\text{mm}^2/(\text{°C} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (\text{°C}) + 1.38$$

($\text{mm}^2/\text{K} \cdot \text{min}$) or more; ~~and~~ or

$$(C) \text{ from } -0.000724 [\text{mm}^2/(\text{°C} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (\text{°C}) + 1.31$$

($\text{mm}^2/\text{K} \cdot \text{min}$) to $-0.000724 [\text{mm}^2/(\text{°C} \cdot \text{K} \cdot \text{min})] \times T_{\text{max}} (\text{°C}) + 1.35 (\text{mm}^2/\text{K} \cdot \text{min})$.

11-13. (Canceled)

14. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein the single crystal is pulled with the $T_{\text{max}} (\text{°C})$ being in a range of 1560 °C or less.

15-17. (Canceled)

18. (Previously Presented) The method for producing a single crystal according to Claim 10, wherein, at least, the $T_{\text{max}} (\text{°C})$ is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

19-21. (Canceled)

22. (Previously Presented) The method for producing a single crystal according to Claim 14, wherein, at least, the $T_{\text{max}} (\text{°C})$ is changed by providing a heat insulating material between the crucible containing the raw material melt and a heater provided so as to surround the crucible, or by providing a heat insulating material below the crucible.

23-25. (Canceled)

26. (Previously Presented) The method of producing a single crystal according to Claim 10, wherein the single crystal that is pulled is a silicon single crystal.

27. (Previously Presented) The method of producing a single crystal according to Claim 10, wherein the single crystal that is pulled has a diameter of 200mm or more.

28. (Canceled)